## **AMENDMENTS TO THE CLAIMS**

1-10 (Cancelled)

11. (New) A method of manufacturing a substrate for a semiconductor substrate, said method comprising:

forming connection terminals on a first surface of the substrate, said first surface corresponding to a surface on which a semiconductor element is to be mounted; and

counterboring a second surface of the substrate that is opposite to the first surface using a cutting blade until the cutting blade contacts the connection terminals so as to expose the connection terminals and form a circuit component mounting hole.

12. (New) The method according to claim 11, further comprising:

forming metal films including connection bumps onto both the first and second surfaces of the substrate,

wherein the metal bumps on the first surface contact the connection terminals.

- 13. (New) The method according to claim 12, wherein the metal films comprises copper films.
  - 14. (New) The method according to claim 11, further comprising:

determining when the cutting blade contacts the connection terminals using a sensor; and

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> controlling a speed of the cutting blade based on the determining step such that the cutting blade cuts into the substrate until the connection terminals are exposed and then stops cutting into the substrate.

15. (New) The method according to claim 11, further comprising:

mounting a circuit component into the circuit component mounting hole such that the circuit component is electrically connected to the connection terminals.

16. (New) The method according to claim 15, further comprising:

mounting a semiconductor element onto the connection terminals on the first surface of the substrate such the semiconductor element is electrically connected to the circuit component.

- 17. (New) The method according to claim 15, wherein the circuit component is a capacitor.
- 18. (New) The method according to claim 11, wherein the component hole is formed in a planar area of the substrate corresponding to semiconductor element area.

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